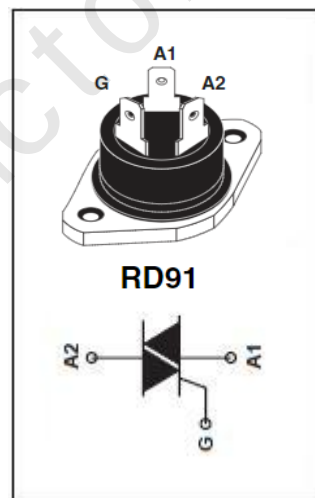


FEATURES

- With RD91 insulated package
 - Suitable for general purpose where high surge current capability is required.
- Application such as phase control and static switching on inductive or resistive load.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	800	V
V_{RRM}	Repetitive peak reverse voltage	800	V
$I_{T(RMS)}$	RMS on-state current (full sine wave) $T_j=90^{\circ}\text{C}$	25	A
I_{TSM}	Non-repetitive peak on-state current $t_p=8.3\text{ms}$	260	A
T_j	Operating junction temperature	125	℃
T_{stg}	Storage temperature	-45~150	℃
$P_{G(AV)}$	Average gate power dissipation($T_j=125^{\circ}\text{C}$)	1	W
$R_{th(j-c)}$	Thermal resistance, junction to case	1.1	℃/W
$R_{th(j-a)}$	Thermal resistance, junction to ambient	50	℃/W


ELECTRICAL CHARACTERISTICS (Tc=25℃ unless otherwise specified)

SYMBOL	PARAMETER		CONDITIONS	MAX	UNIT
I_{RRM}	Repetitive peak reverse current		$V_R=V_{RRM}$, $V_R=V_{RRM}$, $T_j=125^{\circ}\text{C}$	0.01 3.0	mA
I_{DRM}	Repetitive peak off-state current		$V_D=V_{DRM}$, $V_D=V_{DRM}$, $T_j=125^{\circ}\text{C}$	0.01 3.0	mA
I_{GT}	Gate trigger current	I	$V_D=12\text{V}$; $R_L=33\ \Omega$	50	mA
		II		50	
		III		50	
		IV		100	
I_H	Holding current		$I_{GT}=0.5\text{A}$, Gate Open	80	mA
V_{GT}	Gate trigger voltage all quadrant		$V_D=12\text{V}$; $R_L=33\ \Omega$	1.3	V
V_{TM}	On-state voltage		$I_T=35\text{A}$; $t_p=380\ \mu\text{s}$	1.55	V

RD91 Package dimensions

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A		40.00		1.575
A1	29.90	30.30	1.177	1.193
A2		22.00		0.867
B		27.00		1.063
B1	13.50	16.50	0.531	0.650
B2		24.00		0.945
C		14.00		0.551
C1		3.50		0.138
E3	0.70	0.90	0.027	0.035
F	4.00	4.50	0.157	0.177
I	11.20	13.60	0.441	0.535
L1	3.10	3.50	0.122	0.138
L2	1.70	1.90	0.067	0.075
N1	33°	43°	33°	43°
N2	28°	38°	28°	38°